	L#	Hits	Search Text	DBs	Time Stamp
1	L1	7163	(427/526,531,562,564, 595,96,77,123,125).CC LS.	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:20
2	L2·	4443	(438/584,652,622,650, 666,674,685,686,688). CCLS.	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:22
3	L3	5880	FIB focused adj ion adj beam	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:23
4	L4	67	(1 or 2) and 3	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:24

10/084,688

	L #	Hits	Search Text	DBs	Time Stamp
5	L5	610	(1 or 2) and (3 or ion near (beam ray stream))	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:25
6	L6	371	(nano nanometer nanoscale nm) with (metal conductor Al W Pt aluminum tungsten platinum) same(3 or ion near (beam ray stream))	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:32
7	L7	741	(nano nanometer nanoscale nm) with (metal conductor Al W Pt aluminum tungsten platinum) same(sensor)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB	2003/09/0 9 15:32
8	L8	1	5 and 6 and 7	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:34

	L #	Hits	Search Text	DBs	Time Stamp
9	L9	16	6 and 7 not 8	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/09/0 9 15:33
10	L10	4	5 and 7 not (8 or 9)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:35
11	Ľ11	13	5 and 6 not (8 or 9 or 10)	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:36
12	L12	33	10 or 9 or 11	USPA T; US-P GPUB; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/0 9 15:36

	Document	Issue Date	Title	Current OR	Inventor
1	US 2003004 0173 A1	(4/9/0) 13/24/62 2003022 7	Fabrica tion of molecul ar scale devices using fluidic assembl Y	438/622	Fonash, Stephen J. et al.
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	Document ID	Issue Date	Title	Current OR	Inventor	
2	US 2003014 3827 A1	2003073 1	Low area metal contact s for photovo ltaic devices	438/597	Wenham, Stuart Ross et al.	
2	US 2003004 7028 A1	20.03031 3	te metal oxides	75/230 ·	Kunitak e, Toyoki et al.	
8	US 2003003 6204 A1	0	illumin ation system	436/172	Stark, Peter Randolp h Hazard et al.	
4		3 spitter	With Pt-Mn transve rse and longitu dinal	360/324	Lin, Tsann et al.	
5	US 2003002 0060 A1 DIV > 4/2 PN GI	0	ng nano-st ructure s and devices	257/13	Iwasaki , Tatsuya et al.	
	5	US 2003004 7028 A1  US 2003004 7028 A1  US 2003003 6204 A1  US 2003003 5253 A1  US 2003002 0060 A1 DIV > 4/2 PN GI	US 2003014 2003073 2003031 3 2003022 2003003 6204 A1 2003022 2003003 5253 A1 2003022 2003022 2003003 5253 A1 2003022 55 2003002 2003003 5253 A1 2003002 55 20030000 55 20030000 55 20030000 55 20030000 55 20030000 55 20030000 55 20000000000	US 2003014 3827 A1  US 2003004 7028 A1  2003003 6204 A1  2003003 6204 A1  2003003 6204 A1  2003002 0  MRSwsw metal contact s for photovo ltaic devices  Nanomat erials of composi te metal oxides  Surface plasmon enhance dillumin ation system  Magneto resista nce (% ) Whith transve rese and longitu dinal pinning layers, and their fabrica tion method  Nano-st ructure s, process for process	US 2003014 3827 A1  US 2003004 7028 A1  US 2003003 2003003 6204 A1  DIS	

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		Document ID	Issue Date	Title	Current OR	Inventor
	8	\ US 2003000 2226 A1	2003010 2	Fabrica tion method for spin valve sensor with insulat ing and conduct ing seed layers	<b>3</b> 60/314	Lin, Tsann et al.
	Z JB	US 2002019 0251 A1	2002121	Thin film materia ls of amorpho us metal oxides	257/43	Kunitak e, Toyoki et al.
Pull Wheth S.	+ (J (m) 25	JGL, F US 2002010 9134 A1 A+FLB- A	2002081 5 7   here had	NANO-ST RUCTURE S, PROCESS FOR PREPARI NG NANO-ST RUCTURE S AND DEVICES	257/13	Iwasaki , Tatsuya et al.
e pul	9	יי	iloge	Apparat us and a . method for forming an alloy layer over a substra te	438/653	Gavish, Ilan
	10	US 2002005 6816 A1	2002051 6	Surface plasmon enhance d illumin ation system	• 1	Stark, Peter Randolp h Hazard

	Document ID	Issue Date	Title	Current OR	Inventor
H	US 2002001 2797 A1	2002013 1	layer system and product ion method	428/408	Bijkerk , Frederi k et al.
JB 12	Trut pol US 6607779 B2	2003081 9	Nanoted hnology for photonic and optical compone nts	) 427/58	Yadav, Tapesh et al.
13	US 6592725 B2	Hv 2003071 5	Fabrica tion method for spin valve sensor with insulat ing and conduct ing seed layers	204/192	Lin, Tsann et al.
1/4	VS 6562523 B1	2003051 3	Direct write all-gla ss photoma sk blanks	430/5	Wu, Che-Kua ng et al.

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	المحال	US 6548398 B1	2003041 5	Product ion method of semicon ductor device and product ion device therefo	438/622	Yamasak i, Hideaki	
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	17	US 6521098 B1	2003021 8	with insulat ing and conduct ing seed layers	204/192 .11	Lin, Tsann et al.	
??( )! (		Dolymon, IB Tran US 6514453 B2 A Man Sa A Man Sa	2003020	prepare	264/618	Vigliot ti, Anthony et al.	
5,8=	19	US 6476409 B2	2002110 5	Nano-st ructure s, process for prepari ng nano-st ructure s and devices	257/13	Iwasaki , Tatsuya et al.	

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tud (	Ah	form pane	wires	Strongl Y texture	(D7)Far	"R, I	Betchs-
cute als	20 DY	US 6413880 B1	2002070 2 Dens J. Ex. ]	d atomic ridge and dot	438/759	Baski, Alison et al.	$\nearrow$
,	m	be ribes, 10	-sommthem	fabrica tion			
	21	US 6313905 B1	2001110 6	Apparat us and method for definin g a pattern on a substra te	355/55	Brugger , Juergen P. et al.	
·	<b>22</b>	US 6259350 B1	2001071	Sensor and method for manufac turing a sensor	338/25	Mueller -Fiedle r, Roland et al.	
	(Pb)	Ina pod	fur e	mb Pt laser	23 210	Num ···	- Tepsasu
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23 (B	US 6168845 B1	2001010 2 2 2 2 2 2 3 4 3 4 4 5 9	the same using selecti	428/65. 5	Fontana, Jr., Robert Edward et al.
24	US 5912044 A	1999061 5	Method for forming thin film capacit ors	427/79	Farooq, Mukta Shaji et al.

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	(B10	US 5741557 A	1998042 1	Method for deposit ing metal fine lines on a substra te	<b>)</b> 427/469	Corbin, Antoine et al.
' 🖍	<b>2</b> 7	US 5227364 A	1993071 3	Method of forming pattern ed oxide superco nductin g films and Josephs on junctio n devices by using an aqueous alkalin e solutio n	505/329	Fujiwar a, Shuji et al.

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28	ÚS 5192714 A	1993030 9	Method of manufac turing a multila yered metalli zation structu re in which the conduct ive layer and insulat ing layer are selecti vely deposit ed	438/631	Suguro, Kyoichi et al.		
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Pull	30	US 4853341 A	1989080	Process for forming electrodes for semicon ductor devices using focused ion beams	438/625	Nishiok a, Tadashi et al.
	31	US 4782302 A	1988110	Detecto r and energy analyze r for energet ic-hydr ogen in beams and plasmas	204/71	Bastasz , Robert J. et al.
	32	US 4686162 A	•	Optical ly structu red filter and process for its product ion	430/5	Stangl, Gunther et al.
	33		<b>1</b>	Single lithogr aphy for multipl e-layer bubble domain devices	427/96	Ahn, Kie Y. et al.